



# MOSFETs

MOSFETs are available in either depletion/enhancement or enhancement mode (in general, depletion/enhancement devices are operated in the depletion mode and are referred to as depletion devices). They are available in both N- and P-channel, and both single gate and dual gate construction. Some MOSFETs are also offered with input diode protection which reduces the chance of damage from static charge in handling.

TABLE 2. Low-Frequency/Low-Noise (continued)

**P-Channel MOSFETs**

Package TO—	Device	$R_{\theta l} Y_{fsl}$		$C_{iss}$	$C_{rss}$	$V_{(BR)DDS}$	$V_{GS(TH)}$		$I_{DSS}$	
		(mmho) MIN	( $\mu$ mho) MAX	(pF) (MAX)	(pF) MAX	(V) MIN	(V) MIN MAX		(mA) MIN MAX	
72	3N155A	1.0	60	5.0	1.3	-35	-1.5	-3.2	—	-0.25
18	MFE823	1.0	—	6.0	1.5	-50	-3.0	-5.0	—	-0.25
72	MFE3003	—	—	5.0	1.0	-15	—	-4.0	—	10

**N-Channel MOSFETs**

18	2N3796	0.4	1.8	7.0	0.8	25	—	-7.0	2.0	6.0
18	MFE825	0.5	—	4.0	0.7	20	—	—	1.0	25
72	2N4351	1.0	—	5.0	1.3	25	1.0	5.0	—	10
72	3N169	1.0	—	5.0	1.3	25	0.5	1.5	—	10
72	3N170	1.0	—	5.0	1.3	25	1.0	2.0	—	10
72	3N171	1.0	—	5.0	1.3	25	1.5	3.0	—	10
72	MFE3002	—	—	5.0	1.0	15	—	3.0	—	10
18	2N3797	1.5	—	8.0	0.8	25	—	-7.0	2.0	6.0

TABLE 3.

**N-Channel JFETs**

Package TO—	Device	$R_{\theta l} Y_{fsl}$		$R_{\theta l} Y_{osl}$		$C_{iss}$	$C_{rss}$	NF		$V_{(BR)DSS}$ $V_{(BR)GDO}$	$V_{GS(off)}$		$I_{DSS}$	
		(mmho) MIN	@ f (MHz)	( $\mu$ mho) MAX	@ f (MHz)	(pF) (MAX)	(pF) MAX	(dB) MAX	@ RG = 1K f (MHz)	(V) MIN	(V) MIN MAX		(mA) MIN MAX	
92	2N5484	2.5	100	75	100	5.0	1.0	3.0	100	25	0.3	3.0	1.0	5.0
92	2N5485	3.0	400	100	400	5.0	1.0	4.0	400	25	1.0	4.0	4.0	10
92	J305	3.0 <sup>t</sup>	400	80 <sup>t</sup>	100	3.0 <sup>t</sup>	0.8 <sup>t</sup>	4.0 <sup>t</sup>	400	30	0.5	3.0	1.0	8.0
72	2N3823	3.2	200	200	200	6.0	2.0	2.5	100	30	—	8.0	4.0	20
92	2N5486	3.5	400	100	400	5.0	1.0	4.0	400	25	2.0	6.0	8.0	20
72	2N4416	4.0	400	100	400	4.0	0.8	4.0	400	30	2.0	6.0	5.0	15
72	2N4416A	4.0	400	100	400	4.0	0.8	4.0	400	30	2.0	6.0	5.0	15
92	2N5245	4.0	400	100	400	4.5	1.0	4.0	400	30	1.0	6.0	5.0	15
92	J304	4.2 <sup>t</sup>	400	80 <sup>t</sup>	100	3.0 <sup>t</sup>	0.8 <sup>t</sup>	4.0 <sup>t</sup>	400	30	2.0	6.0	5.0	15
52	U310	10	0.001	150	100	5.0	2.5	3 <sup>t</sup>	450	25	2.5	6.0	24	60
92	J308	12 <sup>t</sup>	100	250 <sup>t</sup>	100	7.5	2.5	1.5 <sup>t</sup>	100	25	1.0	6.5	12	60
92	J309	12 <sup>t</sup>	100	250 <sup>t</sup>	100	7.5	2.5	1.5 <sup>t</sup>	100	25	1.0	4.0	12	30
92	J310	12 <sup>t</sup>	100	250 <sup>t</sup>	100	7.5	2.5	1.5 <sup>t</sup>	100	25	2.0	6.5	24	60
72	3N128*	5.0	0.001	500	200	7.0	0.28	5.0	200	-50	-0.5	-8.0	5.0	25

t = typical

\*N-Channel MOSFET